## Notice of References Cited

Application/Control No. 10/695,478	Applicant(s)/Patent Under Reexamination IDOTA ET AL.		
Examiner	Art Unit		
Anh D. Mai	2814	Page 1 of 1	

## U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	А	US-4,318,751	03-1982	Horng, Cheng T.	438/374
	В	US-4,914,053	04-1990	Matyi et al.	438/489
	С	US-4,980,302	12-1990	Shimizu, Junzoh	438/363
	D	US-6,455,364 B1	09-2002	Asai et al.	438/235
	E	US-2004/0157387 A1	08-2004	Yi et al.	438/202
	F	US-2004/0195655 A1	10-2004	Ohnishi et al.	257/575
	G	US-2004/0209418 A1	10-2004	Knoll et al.	438/202
	Н	US-2004/0256613 A1	12-2004	Oda et al.	257/019
		US-2005/0012180 A1	01-2005	Freeman et al.	257/565
	J	US-2005/0048735 A1	03-2005	Khater et al.	438/400
	к	US-			
	L	US-			
	М	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
*	N	JP-2002-305310	10-2002	Japan	Onishi et al.	H01L 21/8222
*	0	JP-2004-241779	08-2004	Japan	Ri et al.	H01L 21/8222
	Ρ					·
	ď					
	R					
	ø					
	T					\

## **NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	D.L. Harame et al., Si/SiGe Epitaxial-Base Transistors - Part II : Process Integration and Analog Applications. IEEE 1995, pp. 469-482.
*	٧	J.A. Babcock et al., Ionizing Radiation of High-Performance SiGe HBT's Grown by UHV/CVD. IEEE 1995, pp. 1558-1566.
	w	
	х	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.